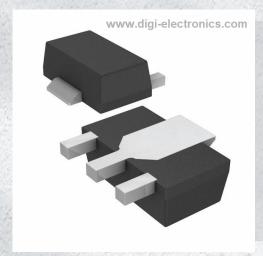


## **PBSS5360XF Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number PBSS5360XF-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBSS5360XF

Description TRANS PNP 60V 3A SOT89

**Detailed Description** Bipolar (BJT) Transistor PNP 60 V 3 A 65MHz 1.35 W

Surface Mount SOT-89



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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### **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PBSS5360XF	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	3 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	550mV @ 300mA, 3A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA	150 @ 50mA, 5V
Power - Max:	Frequency - Transition:
1.35 W	65MHz
Operating Temperature:	Grade:
-55°C ~ 150°C (TA)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
TO-243AA	SOT-89
Base Product Number:	
PBSS5360	

### **Environmental & Export classification**

8541.29.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



# PBSS5360X 60 V, 3 A PNP low VCEsat (BISS) transistor

**Product data sheet** 

#### 1. General description

PNP low V<sub>CEsat</sub> Breakthrough in Smal Signal (BISS) transitor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4360X

#### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_{\text{C}}$  and  $I_{\text{CM}}$
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

#### 3. Applications

- DC-to-DC conversion
- Supply line switches
- · Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	-	-60	V
I <sub>C</sub>	collector current			-	-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	-6	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	225	mΩ

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ 



60 V, 3 A PNP low VCEsat (BISS) transistor

### 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		C
2	С	collector		в
3	В	base	3 2 1	- <b>N</b>
			SOT89	sym132

#### 6. Ordering information

#### Table 3. Ordering information

Type number		Package				
		Name	Description	Version		
PBSS	5360X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

#### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS5360X	S42

2/12

60 V, 3 A PNP low VCEsat (BISS) transistor

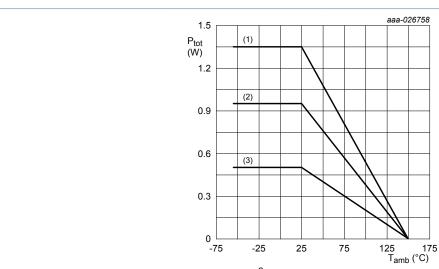
#### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134)

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-80	V
$V_{CEO}$	collector-emitter voltage	open base		-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-6	Α
I <sub>B</sub>	base current			-	-500	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-1	Α
P <sub>tot</sub>	total power dissipation		[1]	-	500	mW
			[2]	-	950	mW
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

60 V, 3 A PNP low VCEsat (BISS) transistor

#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance		[1]	-	-	250	K/W
	from junction to ambient		[2]	-	-	132	K/W
	ambion		<u>[3]</u>	-	-	93	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

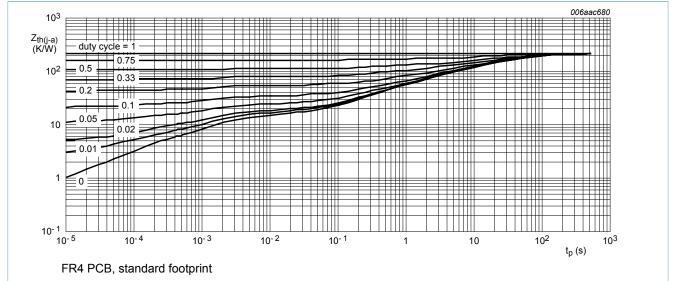


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

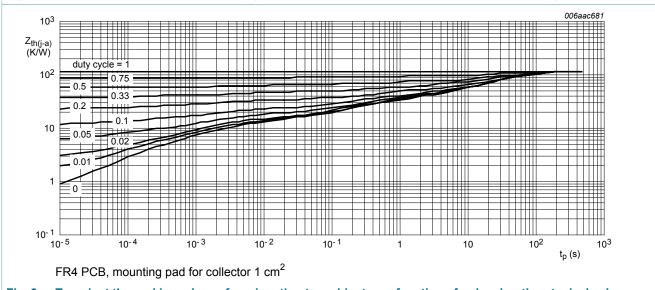
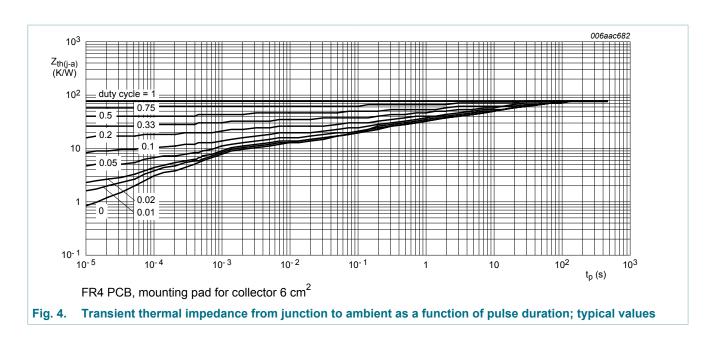


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 60 V, 3 A PNP low VCEsat (BISS) transistor



60 V, 3 A PNP low VCEsat (BISS) transistor

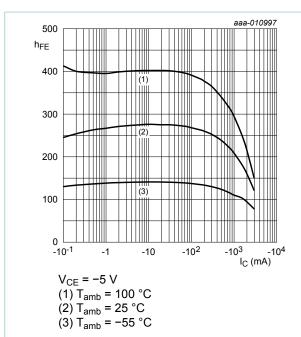
#### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
	current	$V_{CB}$ = -48 V; $I_{E}$ = 0 A; $T_{j}$ = 150 °C		-	-	-50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; $I_{C}$ = 0 A; $T_{amb}$ = 25 °C		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C		150	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C		130	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -1 A; $T_{amb}$ = 25 °C		120	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -2 A; $T_{amb}$ = 25 °C	[1]	100	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -3 A; $T_{amb}$ = 25 °C	[1]	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C		-	-	-150	mV
		$I_C$ = -1 A; $I_B$ = -100 mA; $T_{amb}$ = 25 °C	[1]	-	-	-200	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; $T_{amb}$ = 25 °C	[1]	-	-	-450	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; $T_{amb}$ = 25 °C	[1]	-	-	-550	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = -2 \text{ A}$ ; $I_B = -200 \text{ mA}$ ; $T_{amb} = 25 \text{ °C}$	[1]	-	-	225	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -1 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	-	-	-1.1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C		65	130	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	28	32	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ 

#### 60 V, 3 A PNP low VCEsat (BISS) transistor



DC current gain as a function of collector Fig. 5. current; typical values

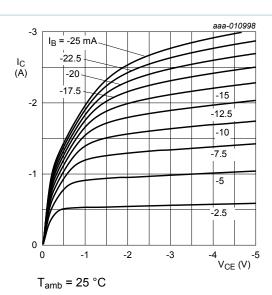


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

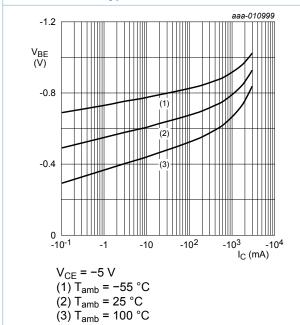
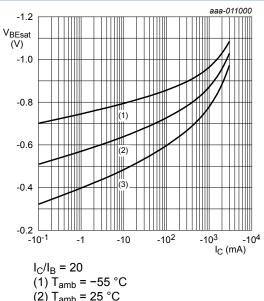


Fig. 7. Base-emitter voltage as a function of collector current; typical values



(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 60 V, 3 A PNP low VCEsat (BISS) transistor

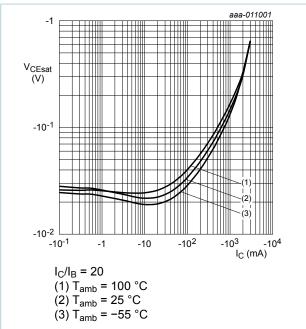


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

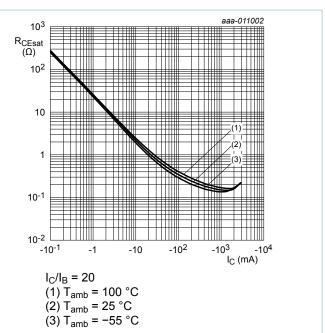


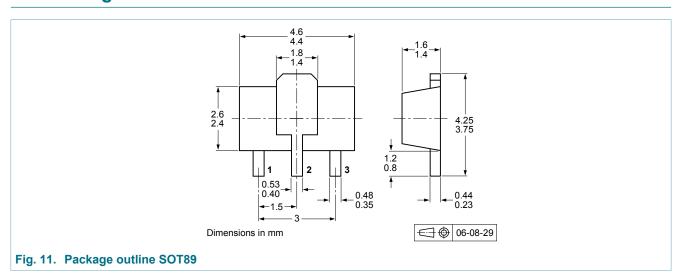
Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

#### 11. Test information

#### **Quality information**

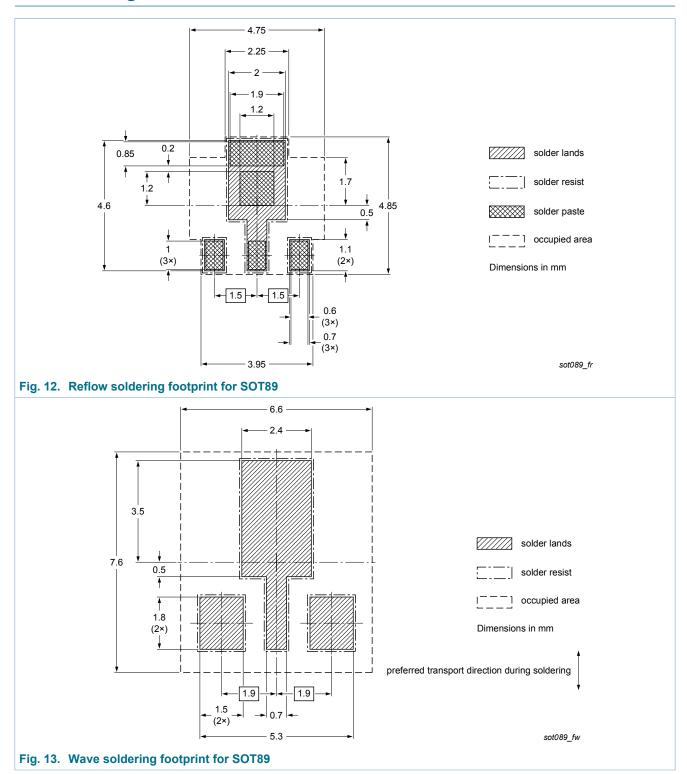
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### 12. Package outline



60 V, 3 A PNP low VCEsat (BISS) transistor

#### 13. Soldering



60 V, 3 A PNP low VCEsat (BISS) transistor

### 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5360X v.1	20170703	Product data sheet	-	-

#### 60 V, 3 A PNP low VCEsat (BISS) transistor

#### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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60 V, 3 A PNP low VCEsat (BISS) transistor

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